

APS MM 2025 in Hong Kong Nanoscale Optoelectronic Materials through Theoretical Modeling



HK Institute of
Quantum Science & Technology
香港量子研究院

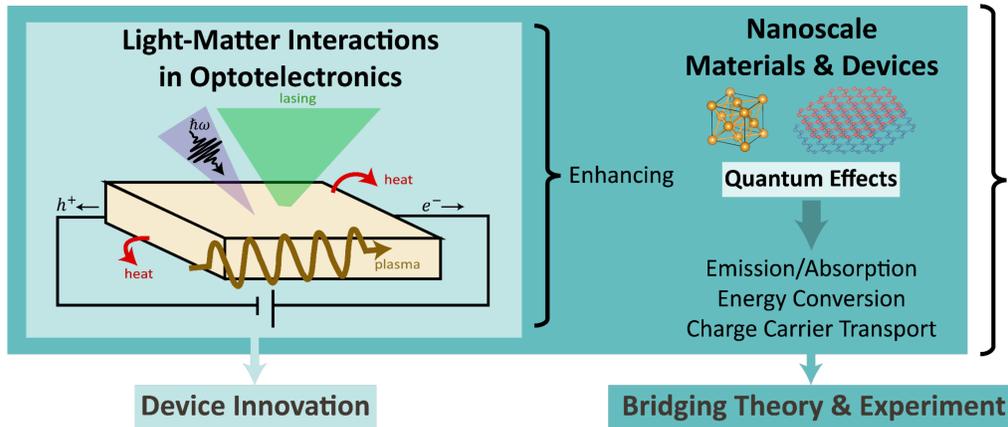
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Lab of Scalable and Sustainable
Photonic Manufacturing

Background and Motivation



First Principle Atomic Scale Density Functional Theory Calculation

Electrical properties

Optical properties

Electrical contacting **unbalance** and limitations to control **contacting properties**:

- 4H-SiC with ALD ZnO

Low-dimensional materials considering **weak interaction** (Van der Waals force):

- mono- and twisted bi-layer graphene

Rationale of Optoelectronic Devices Innovation

Work function Tuning of 4H-SiC by Atomic-level ZnO interlayer

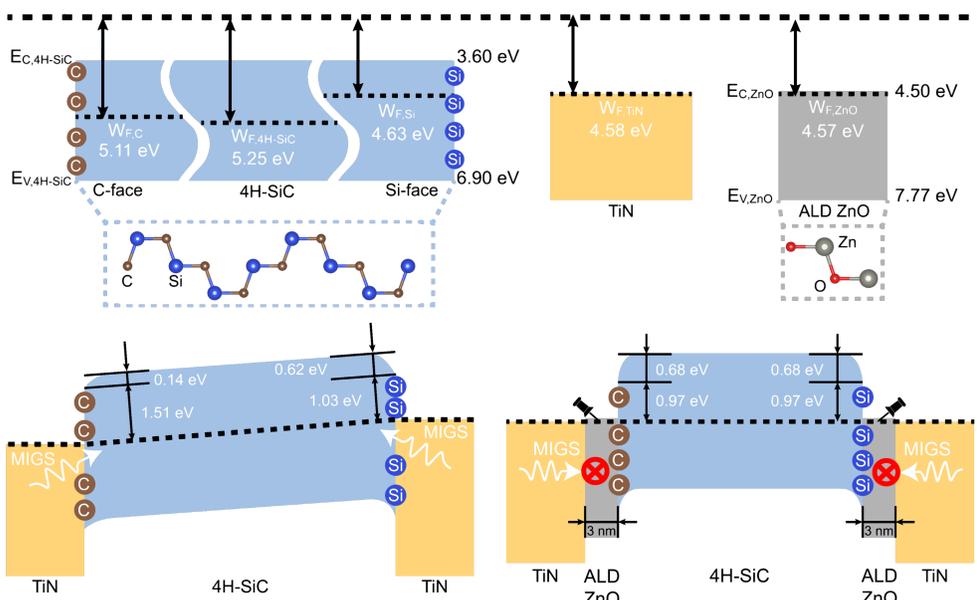
Hexagonal polytypes of SiC (4H-SiC, 6H-SiC):

- Polarity** at atomic layer-by-layer growth surfaces (0001) and (000 $\bar{1}$)
- Dangling unsaturated** sp³ hybridization bonds

Resulting in

- Spontaneous polarization**
- Imbalanced surface potential**
- Strong surface states**

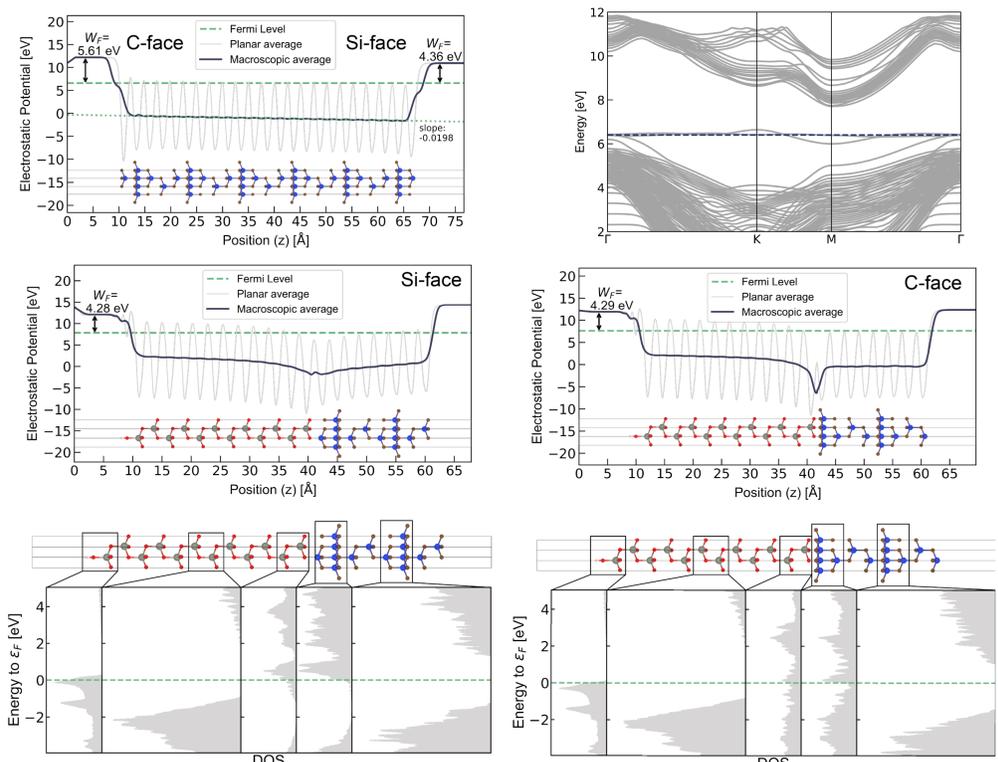
ALD ZnO can solve



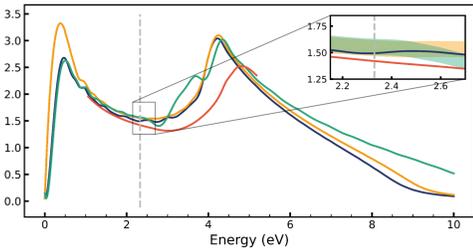
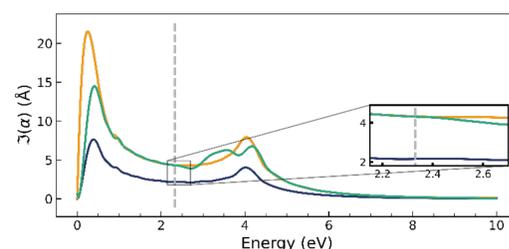
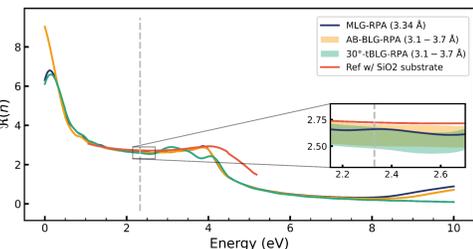
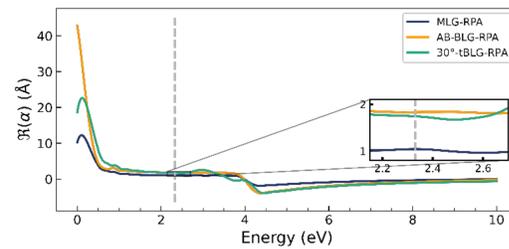
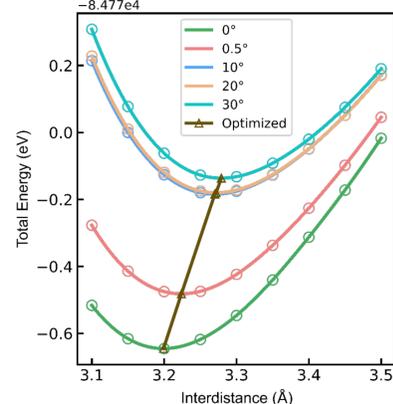
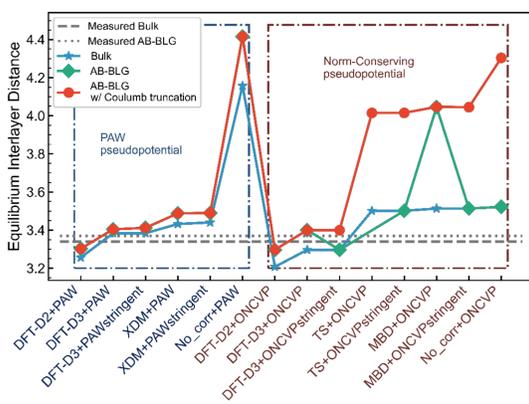
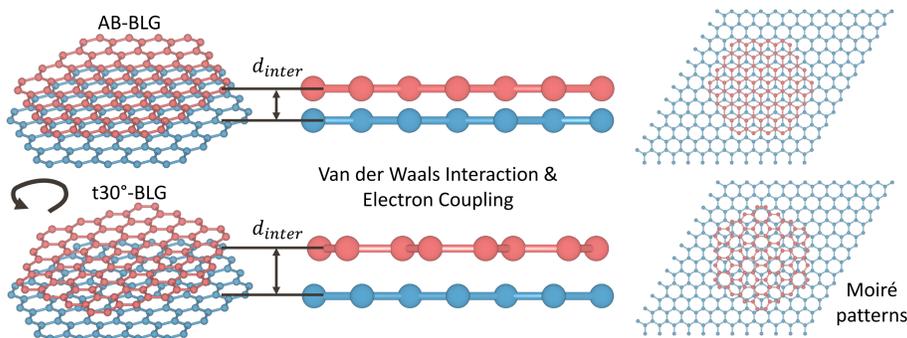
Berry Phase Calculation
(Polarization)

4H-SiC (z-axis 10.11 Å)
1.8965 C/m² per unit cell

ZnO (z-axis 5.20 Å)
0.9176 C/m² per unit cell



Optical Response of Twisted Bilayer Graphene



$$\alpha_{2D}(\omega) = -\lim_{q \rightarrow 0} \frac{L}{4\pi q^2} \chi_{00}(q, \omega) \rightarrow \chi_{00}(\omega) \text{ with certain "thickness"}$$

$$n(\omega) = \sqrt{\epsilon(\omega)} = \sqrt{\chi_{00}(\omega) + 1}$$

Defining "thickness" in 2D materials to predict measurable refractive index